

RGTV60TK65 650V 30A Field Stop Trench IGBT

V _{CES}	650V
I _{C (100°C)}	20A
V _{CE(sat) (Typ.)}	1.5V@I _C =30A
PD	76W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

Solar Inverter

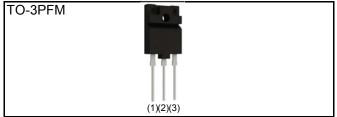
UPS

Welding

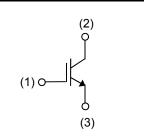
IH

PFC

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGTV60TK65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

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Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_c = 25^{\circ}C$	۱ _C	33	А
Collector Current	$T_c = 100^{\circ}C$	۱ _C	20	А
Pulsed Collector Current		I _{CP} *1	120	А
Power Dissinction	$T_{\rm C}$ = 25°C	P _D	76	W
Power Dissipation	$T_c = 100^{\circ}C$	P _D	38	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	–55 to +175	°C

*1 Pulse width limited by T_{jmax}.

•Thermal Resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	1.97	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA	
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA	
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 21.0mA	5.0	6.0	7.0	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 30A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.5 1.85	1.9 -	V	

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Demonster	Symbol	Conditions	Values				
Parameter	Symbol Conditions -		Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1730	-		
Output Capacitance	C _{oes}	V _{GE} = 0V	-	74	-	pF	
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	30	-		
Total Gate Charge	Qg	V _{CE} = 400V	-	64	-		
Gate - Emitter Charge	Q _{ge}	I _C = 30A	-	14	-	nC	
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	24	-		
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	33	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	12	-		
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	105	-	ns	
Fall Time	t _f	Inductive Load	-	40	-		
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.57	-	ml	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.50	-	mJ	
Turn - on Delay Time	t _{d(on)}	I _C = 30A, V _{CC} = 400V	-	32	-		
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	13	-		
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	121	-	ns	
Fall Time	t _f	Inductive Load	-	80	-		
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.63	-	ml	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.72	-	mJ	
		I _C = 120A, V _{CC} = 520V					
Reverse Bias Safe Operating Area	RBSOA	V _P = 650V, V _{GE} = 15V	FU	LL SQUA	RE	-	
		R _G = 100Ω, T _j = 175°C					
		$V_{CC} \leq 360V$					
Short Circuit Withstand Time	t _{sc}	V _{GE} = 15V	2	-	-	μs	
		T _j = 25°C					

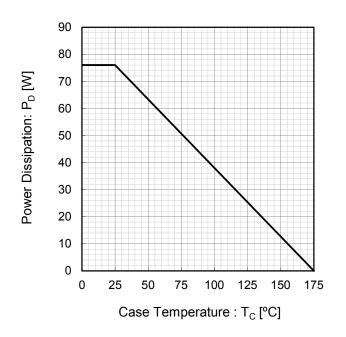


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

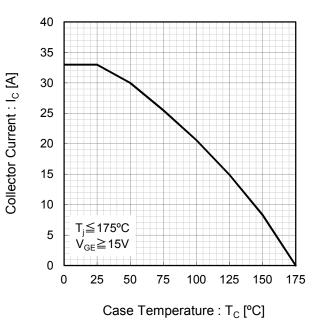
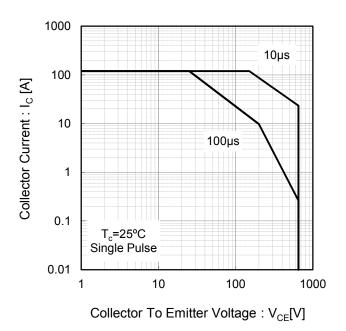
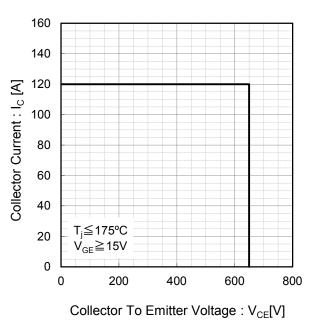


Fig.3 Forward Bias Safe Operating Area







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175

•Electrical Characteristic Curves

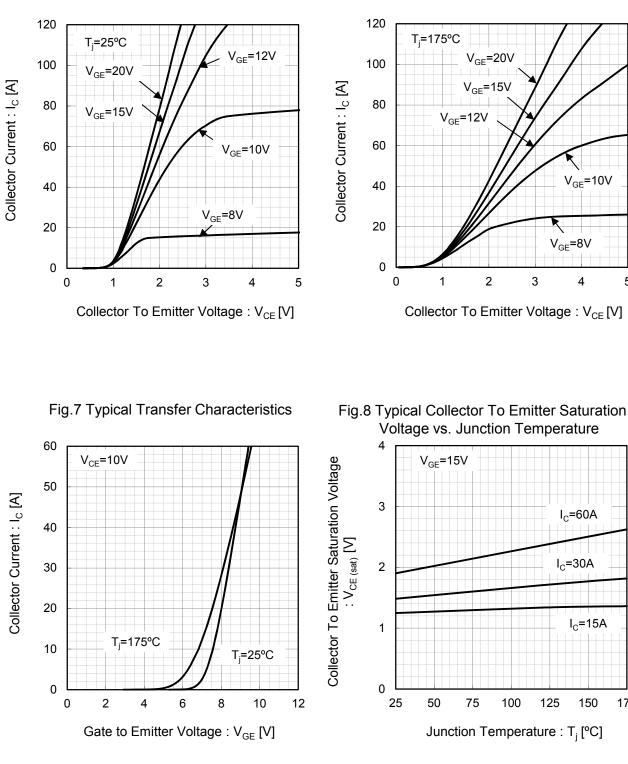
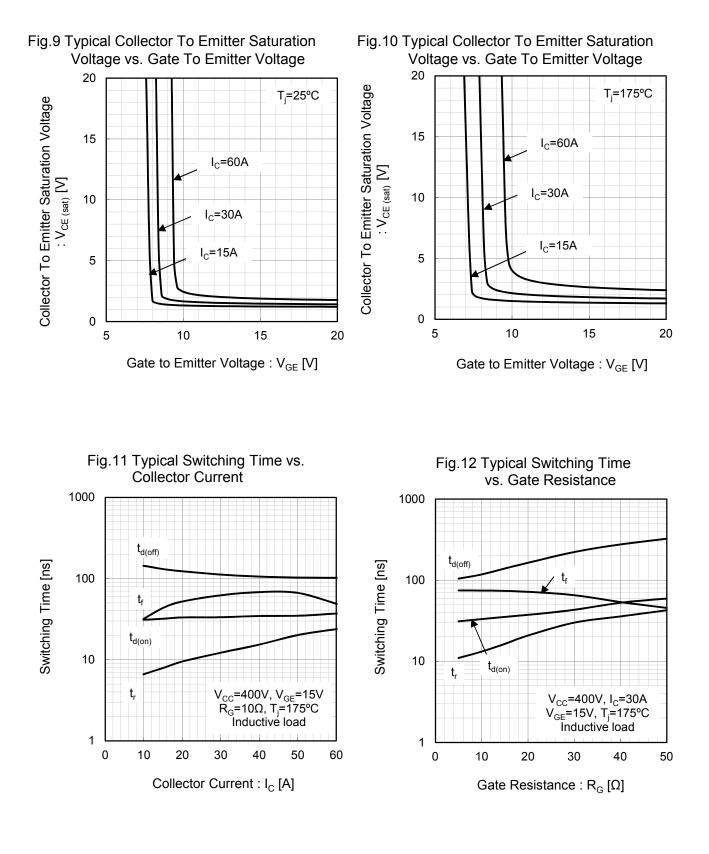
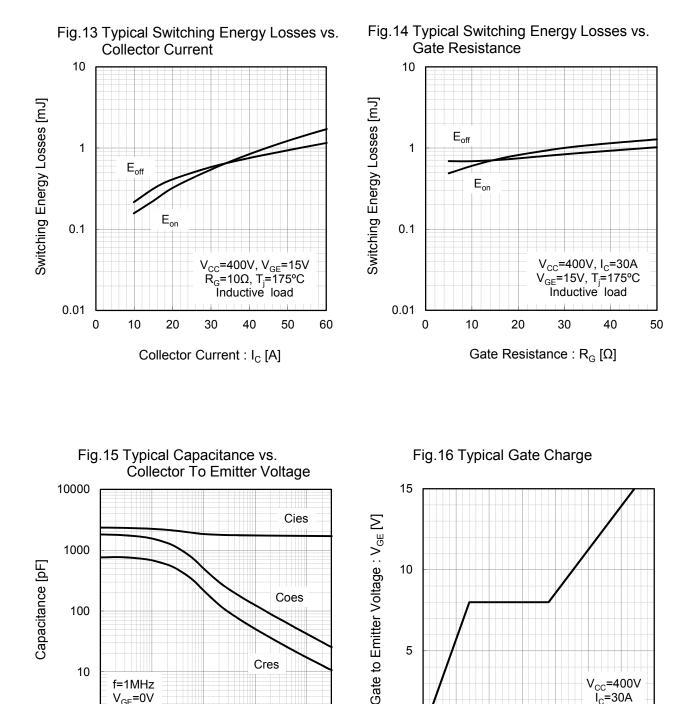


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics





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100

10

1

0.01

f=1MHz V_{GE}=0V

Ti=225℃

0.1

1

Collector To Emitter Voltage : $V_{CE}[V]$

Cres

10

100



V_{CC}=400V I_C=30A

, =25°C

60

70

5

0

0

10

20

30

40

Gate Charge : Q_q[nC]

50

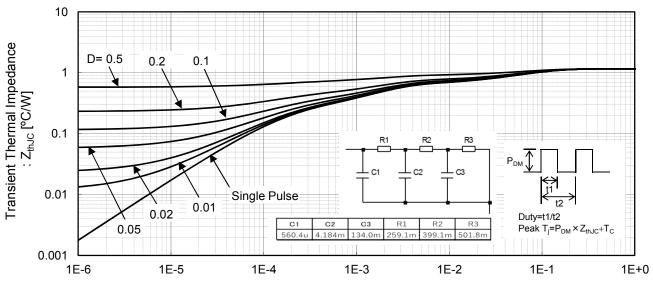
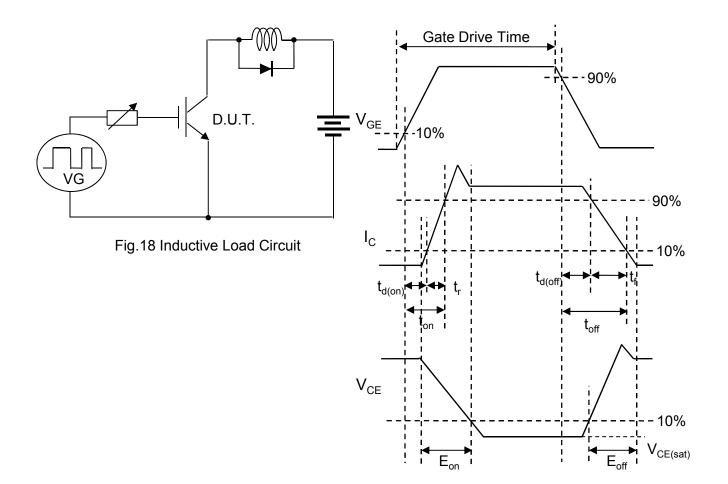
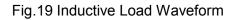


Fig.17 Typical IGBT Transient Thermal Impedance

Pulse Width : t1[s]

Inductive Load Switching Circuit and Waveform





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